

1SS254

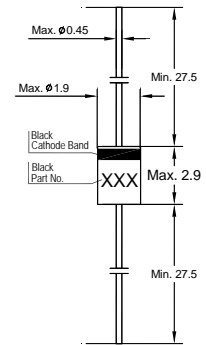
Silicon Epitaxial Planar Switching Diode

Features

- Ultra-high speed
- High withstand voltage
- Low leakage and high voltage

Applications

- High-speed switching



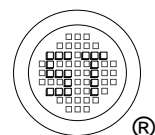
Glass Case DO-34
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	40	V
Reverse Voltage	V_R	35	V
Average Rectified Forward Current	$I_{F(AV)}$	110	mA
Peak Forward Current	I_{FM}	300	mA
Non-Repetitive Peak Forward Surge Current ($t = 1\text{ s}$)	I_{FSM}	400	mA
Junction Temperature	T_j	175	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 175	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 100\text{ mA}$	V_F	1.2	V
Reverse Current at $V_R = 35\text{ V}$	I_R	0.5	μA
Total Capacitance at $V_R = 0.5\text{ V}$, $f = 1\text{ MHz}$	C_{tot}	3	pF
Reverse Recovery Time at $I_F = 10\text{ mA}$, $V_R = 6\text{ V}$	t_{rr}	4	ns



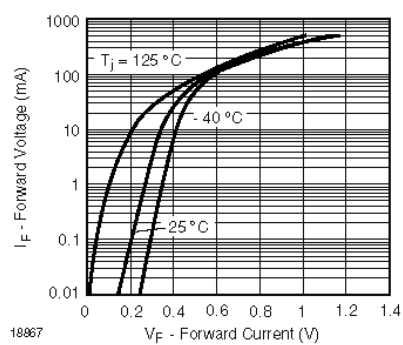


Figure 1. Typical Forward Voltage Forward Current at Various Temperatures

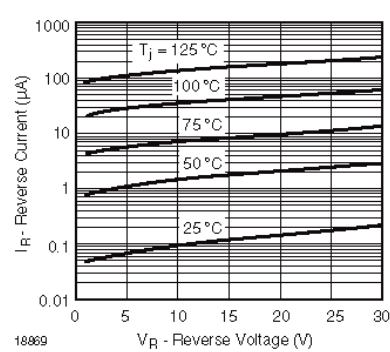


Figure 3. Typical Variation of Reverse Current at Various Temperatures

